Date: 09/12/2025

Minutes of Pre-Bid Meeting

फाइल क्र.: PUR/EQP/82/(2025-26)

विषय: Design and Fabrication of Czochralski Single Crystal Growth System.

A Pre-bid meeting regarding the procurement of instrument was held on 09/12/2025 from 11.00 AM onwards in Saranjamshala.

The following committee members have attend the meeting:

- 1. Dr. Mohd. Akram Khan, Chief Scientist, Head EESD
- 2. Dr. Rajesh Patidar, Principal Scientist, Chairman TSC
- 3. Mr. Nikhil Rajendra Gorhe, Principal Scientist, Member TSC
- 4. Dr. Mohd Shafeeq M, Senior Technical Officer II, Member TSC
- 5. Dr. Vandana, Sr. Principal Scientist & PI, Domain expert
- 6. Dr. Shabi Thankaraj Salammal, Principal Scientist, Indenter

Only Mr. Aadil Khan and Mr. Aakash Abrol from M/s ETL Industrial Heating Systems, Bhopal has attend the pre-bid meeting:

During the pre-bid meeting, firms raised the following queries that have been replied by the committee member:

S/No.	Annexure Points	Request for amendment	Response	
1	-	No tolerance is given in the technical specification such as travel length, chamber dimension, pulling rate. etc	Agreed and tolerances are included throughout the specifications wherever required.	
2	Point Number 7: Qualification criteria	Proven expertise in manufacturing single crystal growth systems under high vacuum (10 ⁻⁴ mbar)/high-vacuum hot presses/high-vacuum stirrers to be made mandatory as the vacuum leak expected through vacuum seal during pulling along with rotation.	Agreed and the qualification criteria was modified as follows: 1. The firm should have prior experience in making single crystal growth systems under high vacuum (≥10 ⁻³ mbar) or high-vacuum hot presses (≥10 ⁻³ mbar) or high-vacuum stirrers (≥10 ⁻³ mbar). Relevant Indian state government/central government/PSUs work order/PO to be enclosed. The operating	

temperature of those systems to be $\geq 1000^{\circ}$ C.
2. No exemption/relaxations will be given in the qualification criteria to MSME's and startup's as this equipment will have high temperature and high vacuum system and safety related issues with public safety, health and its operation.

Other Technical Specifications and terms and conditions of the tender document will remain the same.

Dr. Shabi Thankaraj Salammal (Indenter)

Dr. Vandana (Internal Domain Expert) Dr. Mohd. Akram Khan (HOD)

Dr. Mohd. Shafeeq M (Member)

Mr. Nikhil Rajendra Gorhe (Member)

Dr. Rajesh Patidar (Chairman, TSC)

Annexure -II Revised Specification after pre-bid held on 09/12/2025 Design and Fabrication of Czochralski Single Crystal Growth System

S.No.	Parameter	Technical Specification	
1	Furnace	1. Number of zones: 2	
		2. Continuous operating temperature: 1550°C or more	
		3. ID of furnace: 20 cm ± 1cm	
		4. Temperature accuracy: ±0.5°C or less	
		5. Temperature controller type: PID (Branded)	
		6. To be controlled using: Thyristers (Branded)	
		7. Heating element: Graphite (suitable for vacuum)	
		8. Height of each zone: 20 cm ± 5cm	
		9. Distance between the zone: $2 \text{cm} \pm 0.5 \text{cm}$	
		10. Working atmosphere: 10 ⁻⁵ to 10 ⁻⁶ mbar vacuum and inert	
		atmosphere (Ar or N ₂)	
		11. Thermocouple: B type	
		12. Additional B thermocouple to measure the seed temperature	
2 3 3		which has to move with the seed up and down	
2	Crucible	 Capable of making controlled wobble free rotation Direction of rotation: both clockwise and anticlockwise 	
		directions.	
		3. Stepper motor controlled with gears/similar systems	
		4. RPM: 0.1 to 100 or wider	
		5. High-purity silicon within a fused quartz (SiO ₂)	
91		6. Capacity: 1 kg (Silicon)	
	N 9 3	7. Quantity: 1	
		8. The crucible height to be adjustable for 15 cm \pm 1cm	
3	Growth Chamber	Body: Water cooled and double jacketed corrosion resistant	
-		SS 304	
		2. Vacum tight with double set of O-rings	
		3. Level of vacuum: 10^{-5} to 10^{-6} mbar	
		4. Inlet and outlet valve to be provided for inert gas purging and	
		to grow crystals under various inert atmosphere	
		5. Glass viewing window (To observe melt, crystal growth and	
		seed-melt interface during dipping): 2	
		6. Diameter of viewing window: 10 cm or wider	
		7. Chamber, doors and vacuum seals to be water cooled	
4	Crystal Puller	1. Pulling rate: Variable from 50μm/hr to 1mm/hr or wider	
		2. Wobble free rotation	
		3. Direction of rotation will be with respect to the direction of	
		pulling.	
		4. Controlled movement towards up and down.	
		5. Stepper motor/equivalent motor based pulling system with gears.	
		6. Travel length: 30 cm ± 1 cm	
		7. Option to move entire pulling assembly 20cm ± 1cm up and	
		down to handle easily the seed crystals.	

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		Puller rod to be made of high temperature resist high alumina/graphite rod at the bottom (move in	ant steer Wit side furnace)
5	Gas and Pressure	Solenoid based inlet and outlet valves to be proverystal under various inert ambient.	ided to grow
	Control	A digital flow meter to be provided to control gas	flow.
6	V	Crystal growth pressure will be 2-5 bar. Should be made using the following pumps:	
O	Vacum system	Rotary oil pump: 500 L/min capacity or better Booster pump: ≥ 4000 L/min	
		Diffusion pump (ID): 20 cm or wider	
		Pirani (3 numbers) and penning gauges (one numprovided.	
		Liquid nitrogen trap to be provided ahead of DP back-streaming.	to avoid oil
		Level of vacuum ≈10 ⁻⁶ mbar at the DP mouth. Chamber vacuum: 10 ⁻⁵ mbar – 10 ⁻⁶ mbar	
7	Qualification criteria	government/PSUs work order/PO to be enclos operating temperature of those systems to be ≥ 1000	or high- rrers (≥10 ⁻ ent/central ed. The °C.
		No exemption/relaxations will be given in the question of criteria to MSME's and startup's as this equipment high temperature and high vacuum system and safe issues with public safety, health and its operation.	will have

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